

STPS20L15D/G

LOW DROP OR-ing POWER SCHOTTKY DIODE

MAIN PRODUCT CHARACTERISTICS

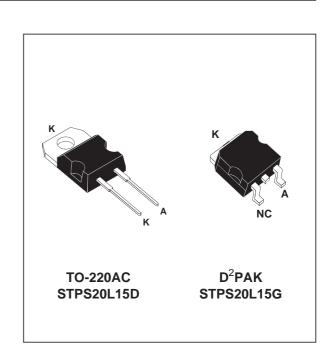
I _{F(AV)}	20 A
V _{RRM}	15 V
Tj (max)	125°C
V _F (max)	0.33 V

FEATURES AND BENEFITS

- VERY LOW FORWARD VOLTAGE DROP FOR LESS POWER DISSIPATION AND REDUCED HEATSINK SIZE
- REVERSE VOLTAGE SUITED TO OR-ing OF 3V, 5V and 12V RAILS
- AVALANCHE CAPABILITY SPECIFIED

DESCRIPTION

Packaged in TO-220AC or D²PAK, this device is especially intended for use as an OR-ing diode in fault tolerant power supply equipments.



ABSOLUTE RATINGS (limiting values)

Symbol	Parameter	Value	Unit	
V_{RRM}	Repetitive peak reverse voltage		15	V
I _{F(RMS)}	RMS forward current		30	Α
I _{F(AV)}	Average forward current	Tc = 115°C δ = 1	20	Α
I _{FSM}	Surge non repetitive forward current	tp = 10 ms Sinusoidal	310	Α
I _{RRM}	Repetitive peak reverse current $tp = 2 \mu s F = 1 kHz$		2	Α
I _{RSM}	Non repetitive peak reverse current tp = 100 µs		3	Α
P _{ARM}	Repetitive peak avalanche power tp = 1µs Tj = 25°C		13500	W
T _{stg}	Storage temperature range	- 65 to + 150	°C	
Tj	Maximum operating junction temperatur	125	°C	
dV/dt	Critical rate of rise of reverse voltage	10000	V/µs	

^{* :} $\frac{dPtot}{dTj} < \frac{1}{Rth(j-a)}$ thermal runaway condition for a diode on its own heatsink

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th (j-c)}	Junction to case	1.6	°C/W

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STATIC ELECTRICAL CHARACTERISTICS

Symbol	Tests Conditions	Tests Conditions		Min.	Тур.	Max.	Unit
I _R *	Reverse leakage	Tj = 25°C	V _R = 15V			6	mA
	current	Tj = 100°C	V _R = 15V		200	500	
V _F *	Forward voltage drop	Tj = 25°C	I _F = 19 A			0.41	V
		Tj = 25°C	I _F = 40 A			0.52	
		Tj = 125°C	I _F = 19 A		0.28	0.33	
		Tj = 125°C	I _F = 40 A		0.42	0.50	

Pulse test : * tp = 380 μ s, δ < 2%

To evaluate the maximum conduction losses use the following equation :

 $P = 0.18 \times I_{F(AV)} + 8.10^{-3} \times I_{F}^{2}(RMS)$

Fig. 1: Average forward power dissipation versus average forward current.

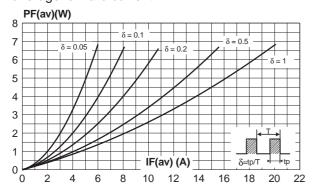


Fig. 3: Normalized avalanche power derating versus pulse duration.

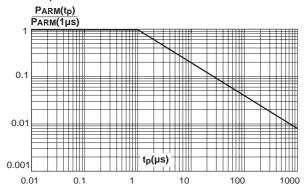


Fig. 5: Non repetitive surge peak forward current versus overload duration (maximum values).

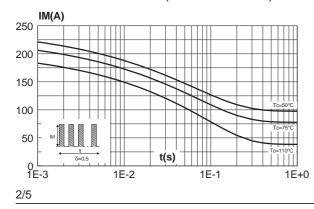


Fig. 2: Average forward current versus ambient temperature ($\delta = 1$).

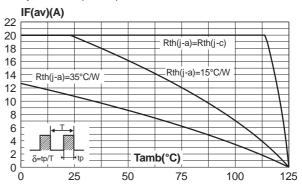


Fig. 4: Normalized avalanche power derating versus junction temperature.

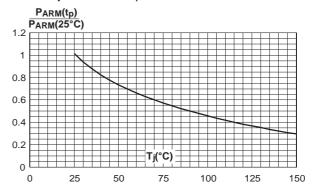


Fig. 6: Relative variation of thermal impedance junction to case versus pulse duration.

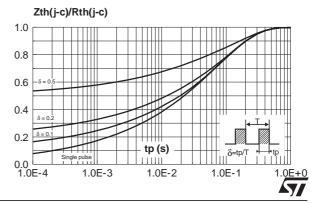


Fig. 7: Reverse leakage current versus reverse voltage applied (typical values).

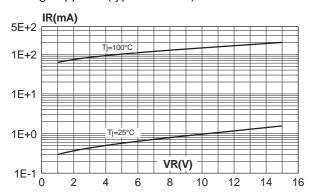


Fig. 8: Junction capacitance versus reverse voltage applied (typical values).

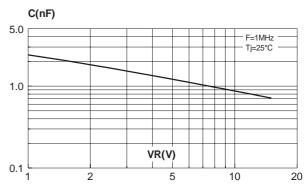


Fig. 9: Forward voltage drop versus forward current (typical values).

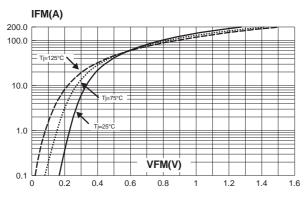


Fig. 10: Forward voltage drop versus forward current (maximum values).

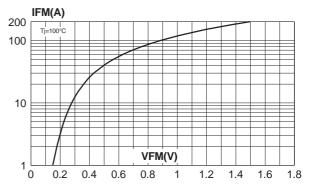
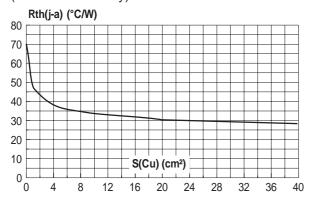
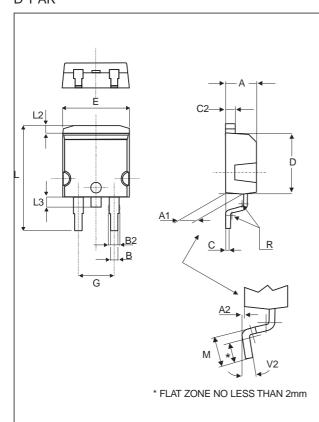


Fig. 11: Thermal resistance junction to ambient versus copper surface under tab (Epoxy printed circuit board FR4, copper thickness : $35 \, \mu m$). (STPS20L15G only)



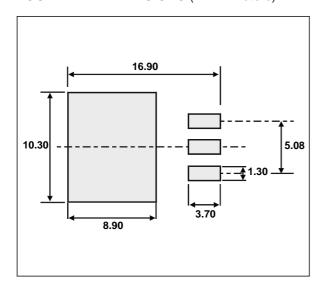
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$\begin{array}{c} \textbf{PACKAGE MECHANICAL DATA} \\ \textbf{D}^2 \textbf{PAK} \end{array}$



	DIMENSIONS				
REF.	Millim	eters	Inches		
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
A1	2.49	2.69	0.098	0.106	
A2	0.03	0.23	0.001	0.009	
В	0.70	0.93	0.027	0.037	
B2	1.14	1.70	0.045	0.067	
С	0.45	0.60	0.017	0.024	
C2	1.23	1.36	0.048	0.054	
D	8.95	9.35	0.352	0.368	
Е	10.00	10.40	0.393	0.409	
G	4.88	5.28	0.192	0.208	
L	15.00	15.85	0.590	0.624	
L2	1.27	1.40	0.050	0.055	
L3	1.40	1.75	0.055	0.069	
М	2.40	3.20	0.094	0.126	
R	0.40 typ.		0.016 typ.		
V2	0°	8°	0° 8°		

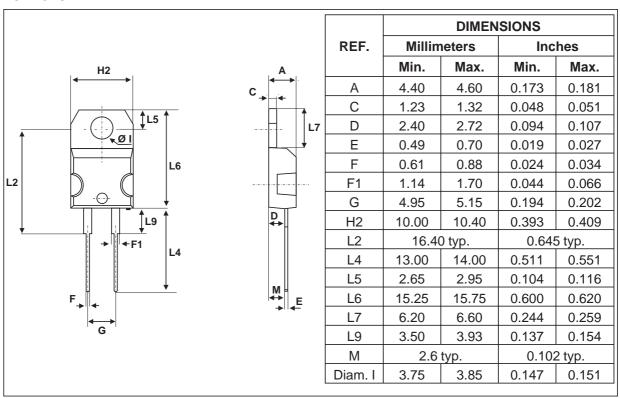
FOOT PRINT DIMENSIONS (in millimeters)



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PACKAGE MECHANICAL DATA

TO-220AC



Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS20L15D	STPS20L15D	TO-220AC	1.86 g.	50	Tube
STPS20L15G	STPS20L15G	D ² PAK	1.48g.	50	Tube
STPS20L15G-TR	STPS20L15G	D ² PAK	1.48 g.	1000	Tape and reel

Cooling method: by conduction (C)Recommended torque value: 0.55 m.N

Maximum torque value: 0.7 m.N

Epoxy meets UL94,V0

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